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(54) **INTEGRATED CIRCUIT DEVICE**

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(57) **ABSTRACT**

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An integrated circuit device includes: a substrate including a plurality of active regions; a bit line extending on the substrate in a horizontal direction; a direct contact connected between a first active region selected among the plurality of active regions and the bit line; an inner oxide layer contacting a sidewall of the direct contact; and a carbon-containing oxide layer nonlinearly extending on a sidewall of the bit line in a vertical direction, the carbon-containing oxide layer contacting the sidewall of the bit line.

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